

High voltage switching diode

BAS21N3

Description

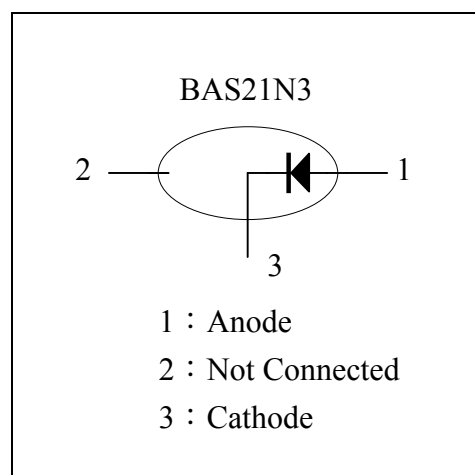
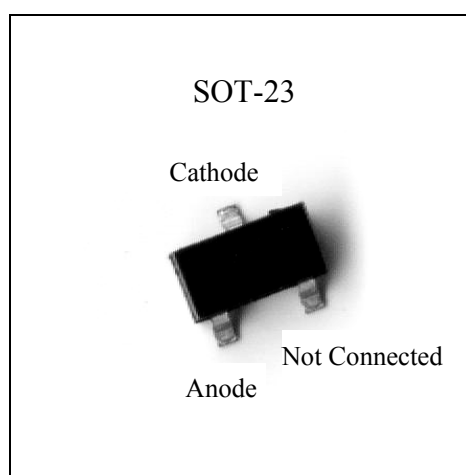
The BAS21N3 is a general purpose diode fabricated in planar technology and encapsulated in a small SOT-23 plastic SMD package.

Features

- Fast switching speed : max. 50ns
- Small plastic SMD package
- General application.
- Continuous reverse voltage : max. 200V
- Repetitive peak reverse voltage : max. 250V
- Repetitive peak forward current : max. 625mA

Applications

- General purpose switching in e.g. surface mounted circuits.

Symbol**Outline**

**Absolute Maximum Ratings @ $T_A=25^{\circ}\text{C}$**

Parameter Sym	bol	Min	Max	Unit
Repetitive peak reverse voltage	V_{RRM}	-	250	V
Continuous reverse voltage	V_R	-	200	V
Continuous forward current	I_F	-	200	mA
Repetitive peak forward current	I_{FRM}		625	mA
Non-repetitive peak forward current @square wave, $T_j=25^{\circ}\text{C}$ prior to surge	I_{FSM}	$t=1\mu\text{s}$	9	A
		$t=100\mu\text{s}$	3	A
		$t=10\text{ms}$	1.7	A
Total power dissipation(Note 1) P_{tot}			250	mW
Junction Temperature	T_j	-	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-65	+150	$^{\circ}\text{C}$

Note 1: Device mounted on an FR-4 PCB.

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameters Sym	bol	Conditions	Min	Typ.	Max	Unit
Forward voltage	V_F	$I_F=100\text{mA}$ $I_F=200\text{mA}$	-		1 1.25	V V
Reverse current	I_R	$V_R=200\text{V}$ $V_R=200\text{V}, T_j=150^{\circ}\text{C}$	-		100 100	nA μA
Diode capacitance	C_d	$V_R=0\text{V}, f=1\text{MHz}$	-	-	5	pF
Reverse recovery time	t_{rr}	when switched from $I_F=30\text{mA}$ to $I_R=30\text{mA}, R_L=100\Omega$, measured at $I_R=3\text{mA}$	-	-	50	ns

Thermal Characteristics

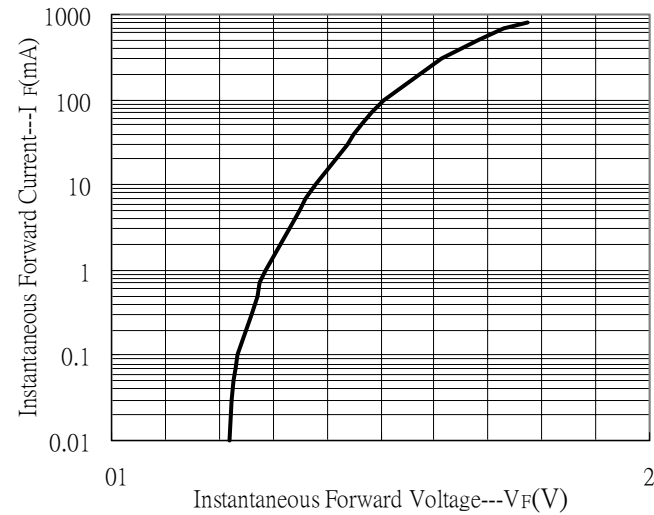
Symbol	Parameter	Conditions	Value	Unit
$R_{th,j-tp}$	thermal resistance from junction to tie-point		330	$^{\circ}\text{C}/\text{W}$
$R_{th,j-a}$	thermal resistance from junction to ambient	Note 1	500	$^{\circ}\text{C}/\text{W}$

Note 1: Device mounted on an FR-4 PCB.

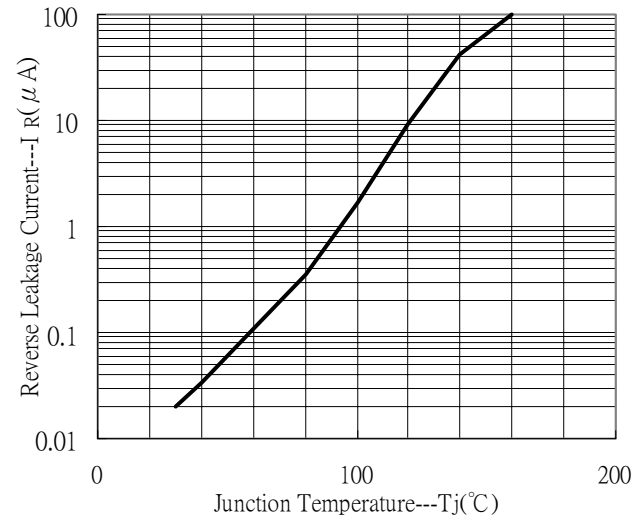


Characteristic Curves

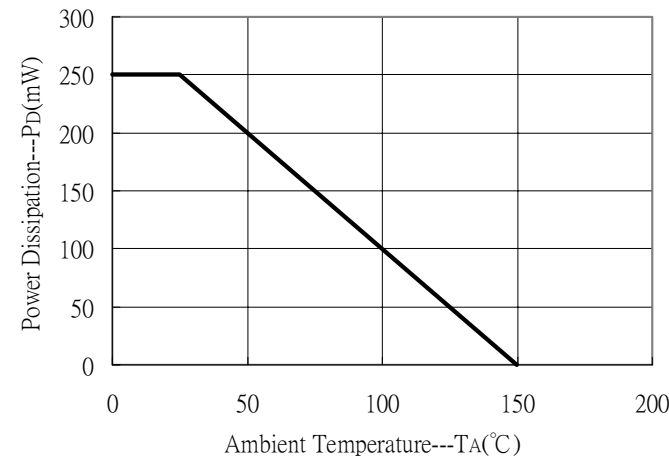
Forward Characteristics



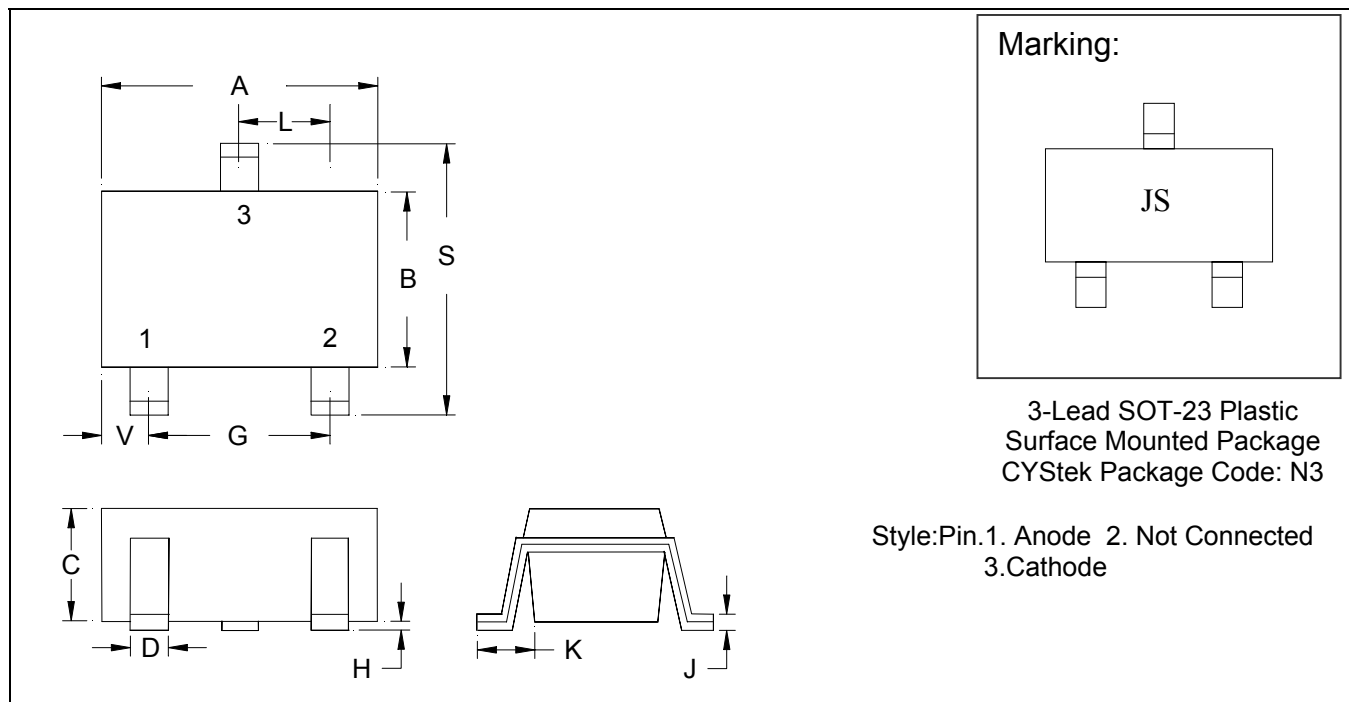
Reverse Leakage Current vs Junction Temperature



Power Derating Curve



SOT-23 Dimension



*: Typical

DIM	Inches Millimeters				DIM	Inches Millimeters			
	Min.	Max	Min.	Max		Min.	Max	Min.	Max
A	0.102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1. Controlling dimension: millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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